ALPHA & OMEGA SEMICONDUCTOR, INC.

Nov 2002

AO7405
P-Channel Enhancement Mode Field Effect Transistor

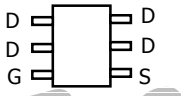
General Description

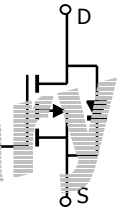
The AO7405 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge, and operation with gate voltages as low as 2.5V, in the small SOT363 footprint. It can be used for a wide variety of applications, including load switching, low current inverters and low current DC-DC converters.

Features

V_{DS} (V) = -30V
I_D = -1.6A
$R_{DS(ON)}$ < 150mΩ (V_{GS} = -10V)
$R_{DS(ON)}$ < 200mΩ (V_{GS} = -4.5V)
$R_{DS(ON)}$ < 280mΩ (V_{GS} = -2.5V)

SC-70-6
(SOT-363)
Top View





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current [A]	T_A=25°C	I_D	-1.6	A
	T_A=70°C		-1.3	
Pulsed Drain Current [B]		I_{DM}	-10	
Power Dissipation [A]	T_A=25°C	P_D	0.625	W
	T_A=70°C		0.4	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$		200	°C/W
Maximum Junction-to-Ambient [A]	Steady-State			220	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$			°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-24V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±12V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-0.6	-1	-1.4	V
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V	-10			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-1.6A		115	150	mΩ
		T_J=125°C				
		V_{GS}=-4.5V, I_D=-1A		135	200	mΩ
		V_{GS}=-2.5V, I_D=-1A		190	280	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-1.2A	3	4.5		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.85	-1	V
I_S	Maximum Body-Diode Continuous Current				-0.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz		409		pF
C_{oss}	Output Capacitance			55		pF
C_{rss}	Reverse Transfer Capacitance			42		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		12		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-15V, I_D=-1A		5.06		nC
Q_{gs}	Gate Source Charge			0.72		nC
Q_{gd}	Gate Drain Charge			1.58		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=15Ω, R_{GEN}=3Ω		6.2		ns
t_r	Turn-On Rise Time			3.2		ns
$t_{D(off)}$	Turn-Off DelayTime			41.2		ns
t_f	Turn-Off Fall Time			14.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-1A, dI/dt=100A/µs		13.2		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-1A, dI/dt=100A/µs		5.4		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.